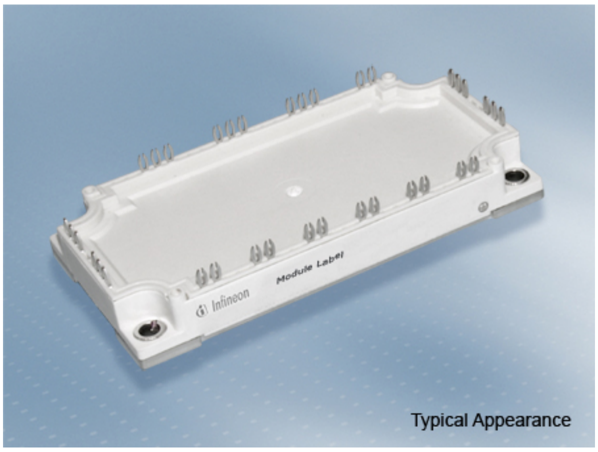
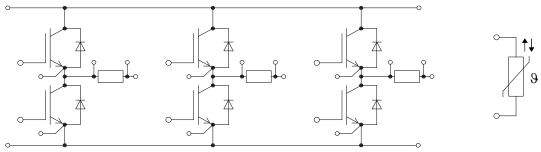
IFS150B17N3E4P_B11

MIPAQ™base 模块 采用第四代沟槽栅/场终止IGBT4和发射极控制二极管 带有pressfit预涂导热材料
MIPAQ™base module with Trench/Fieldstop IGBT4 and Emitter Controlled diode and PressFIT / pre-applied Thermal Interface Material





V_{CES} = 1700V
$I_{C\,nom}$ = 150A / I_{CRM} = 300A

典型应用
- 电机传动
- UPS系统

Typical Applications
- Motor drives
- UPS systems

电气特性
- 提高工作结温 $T_{vj\,op}$
- 低 V_{CEsat}
- V_{CEsat} 带正温度系数

Electrical Features
- Extended operating temperature $T_{vj\,op}$
- Low V_{CEsat}
- V_{CEsat} with positive temperature coefficient

机械特性
- 集成NTC温度传感器
- 绝缘的基板
- 焊接技术
- 标准封装
- 预涂导热介质

Mechanical Features
- Integrated NTC temperature sensor
- Isolated base plate
- Solder contact technology
- Standard housing
- Pre-applied Thermal Interface Material

Module Label Code

Barcode Code 128

00000123456000000000000

DMX - Code

Content of the Code	**Digit**
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT,Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1700	V
连续集电极直流电流 Continuous DC collector current	T_H = 80°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$	150	A
集电极重复峰值电流 Repetitive peak collector current	t_P = 1 ms	I_{CRM}	300	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

				min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	I_C = 150 A, V_{GE} = 15 V I_C = 150 A, V_{GE} = 15 V I_C = 150 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE\,sat}$		1,95 2,35 2,45	2,30	V V V
栅极阈值电压 Gate threshold voltage	I_C = 6,00 mA, V_{CE} = V_{GE}, T_{vj} = 25°C		V_{GEth}	5,25	5,80	6,35	V
栅极电荷 Gate charge	V_{GE} = -15 V ... +15 V		Q_G		1,70		µC
内部栅极电阻 Internal gate resistor	T_{vj} = 25°C		R_{Gint}		5,0		Ω
输入电容 Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		13,5		nF
反向传输电容 Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{res}		0,44		nF
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE} = 1700 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	I_C = 150 A, V_{CE} = 900 V V_{GE} = ±15 V R_{Gon} = 0,24 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,on}$		0,20 0,22 0,23		µs µs µs
上升时间(电感负载) Rise time, inductive load	I_C = 150 A, V_{CE} = 900 V V_{GE} = ±15 V R_{Gon} = 0,24 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0,03 0,04 0,04		µs µs µs
关断延迟时间(电感负载) Turn-off delay time, inductive load	I_C = 150 A, V_{CE} = 900 V V_{GE} = ±15 V R_{Goff} = 0,24 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,off}$		0,40 0,55 0,59		µs µs µs
下降时间(电感负载) Fall time, inductive load	I_C = 150 A, V_{CE} = 900 V V_{GE} = ±15 V R_{Goff} = 0,24 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0,09 0,15 0,17		µs µs µs
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	I_C = 150 A, V_{CE} = 900 V, L_S = 30 nH V_{GE} = ±15 V, di/dt = 4500 A/µs (T_{vj} = 150°C) R_{Gon} = 0,24 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		25,0 36,0 39,5		mJ mJ mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	I_C = 150 A, V_{CE} = 900 V, L_S = 30 nH V_{GE} = ±15 V, du/dt = 3100 V/µs (T_{vj} = 150°C) R_{Goff} = 0,24 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		27,0 44,0 49,5		mJ mJ mJ
短路数据 SC data	V_{GE} ≤ 15 V, V_{CC} = 1000 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt	t_P ≤ 10 µs, T_{vj} = 150°C	I_{SC}		700		A
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个 IGBT / per IGBT valid with IFX pre-applied thermal interface material		R_{thJH}			0,206	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

二极管,逆变器 / Diode, Inverter

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1700	V
连续正向直流电流 Continuous DC forward current		I_F	150	A
正向重复峰值电流 Repetitive peak forward current	t_P = 1 ms	I_{FRM}	300	A
I2t-值 I^2t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I^2t	3800 3700	A^2s A^2s

特征值 / Characteristic Values

				min.	typ.	max.	
正向电压 Forward voltage	I_F = 150 A, V_{GE} = 0 V I_F = 150 A, V_{GE} = 0 V I_F = 150 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,80 1,90 1,95	2,20	V V V
反向恢复峰值电流 Peak reverse recovery current	I_F = 150 A, - di_F/dt = 4500 A/µs (T_{vj}=150°C) V_R = 900 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		275 280 285		A A A
恢复电荷 Recovered charge	I_F = 150 A, - di_F/dt = 4500 A/µs (T_{vj}=150°C) V_R = 900 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		45,0 60,5 68,0		µC µC µC
反向恢复损耗(每脉冲) Reverse recovery energy	I_F = 150 A, - di_F/dt = 4500 A/µs (T_{vj}=150°C) V_R = 900 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		23,0 36,0 40,5		mJ mJ mJ
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material		R_{thJH}			0,404	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

电流取样电阻 / Shunt

			min.	typ.	max.	
额定电阻值 Rated resistance	T_c = 20°C	R_{20}		1,50		mΩ
温度系数(tcr) Temperature coefficient (tcr)	20°C - 60°C			< 30		ppm/K
电流取样电阻工作温度 Operation temperature shunt-resistor		T_{tvjop}			200	°C
结 - 散热器热阻 Thermal resistance, junction to heatsink		R_{thJH}			9,7	K/W

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	T_{NTC} = 25°C	R_{25}		5,00		kΩ
R100 偏差 Deviation of R100	T_{NTC} = 100°C, R_{100} = 493 Ω	ΔR/R	-5		5	%
耗散功率 Power dissipation	T_{NTC} = 25°C	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\ K))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\ K))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\ K))]$	$B_{25/100}$		3433		K

根据应用手册标定
Specification according to the valid application note.

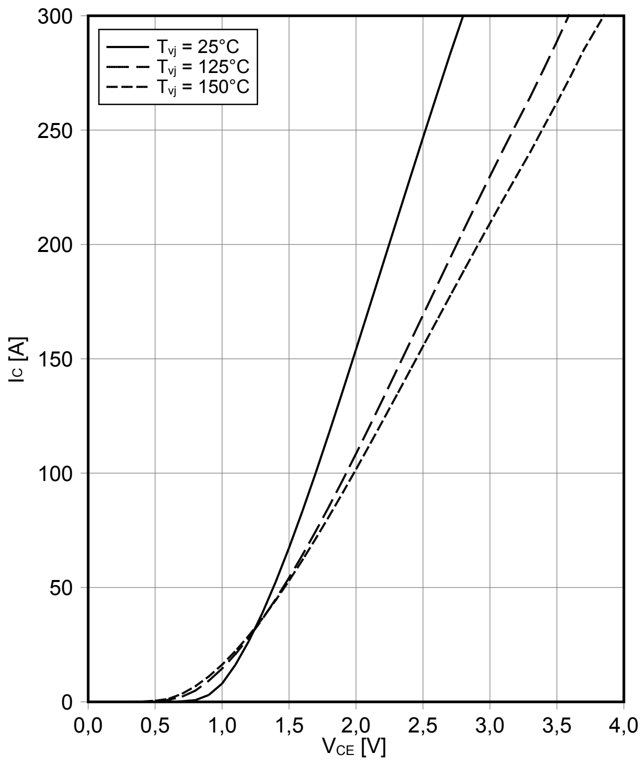
模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}	3,4		kV
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al_2O_3		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		10,0		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		7,5		mm
相对电痕指数 Comperative tracking index		CTI	> 200		

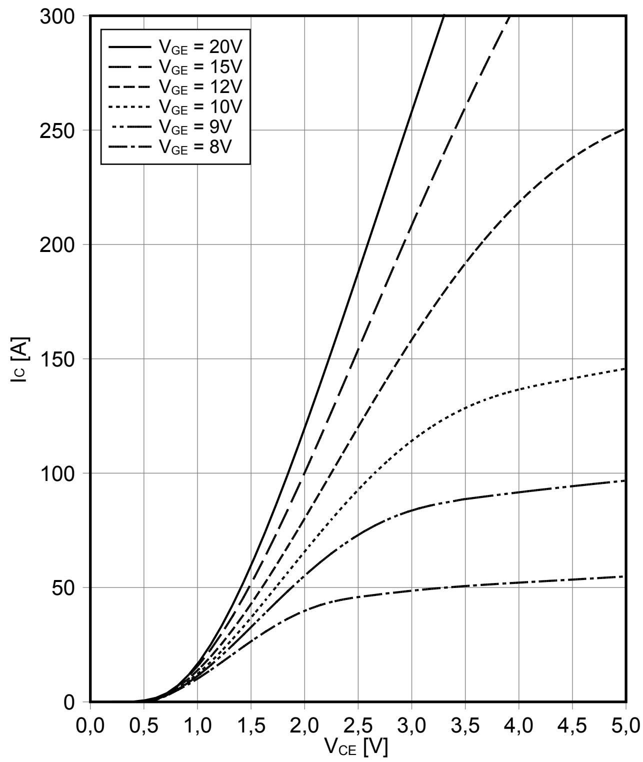
			min.	typ.	max.	
杂散电感,模块 Stray inductance module		L_{sCE}		20		nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T_H = 25°C, 每个开关 / per switch	$R_{CC'+EE'}$		2,50		mΩ
储存温度 Storage temperature		T_{stg}	-40		125	°C
最高基板工作温度 Maximum baseplate operation temperature		T_{BPmax}			125	°C
模块安装的安装扭距 Mounting torque for modul mounting	螺丝 M5 根据相应的应用手册进行安装 Screw M5 - Mounting according to valid application note	M	3,00		6,00	Nm
重量 Weight		G		300		g

Lagerung und Transport von Modulen mit TIM => siehe AN2012-07
Storage and shipment of modules with TIM => see AN2012-07

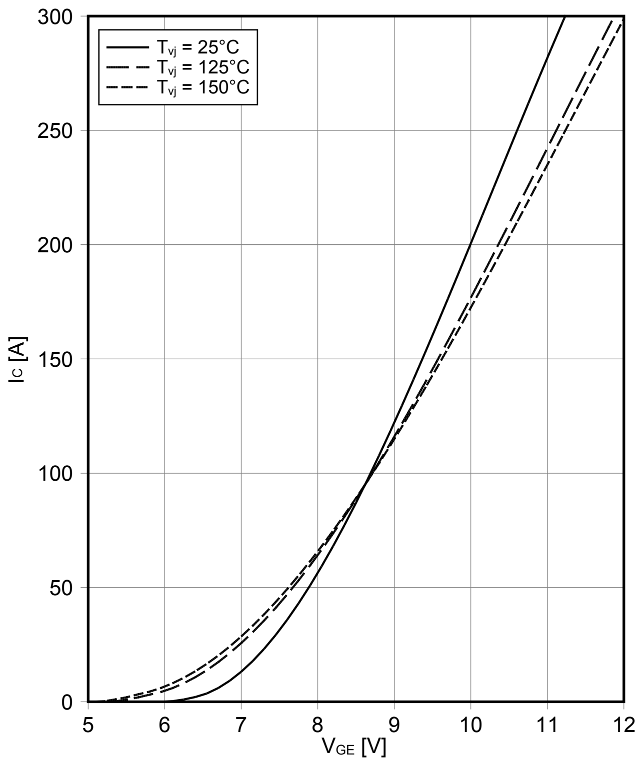
输出特性 IGBT, 逆变器 （典型)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V



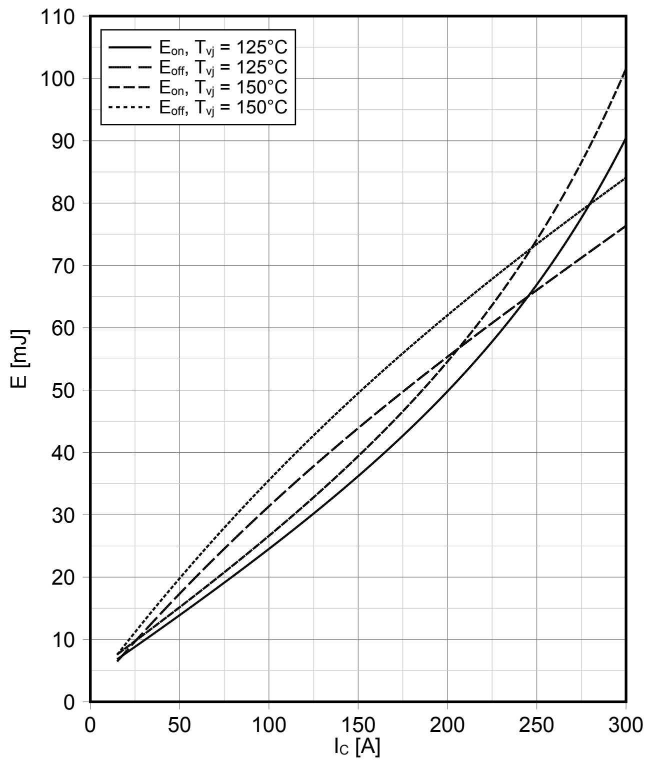
输出特性 IGBT, 逆变器 （典型)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150$°C



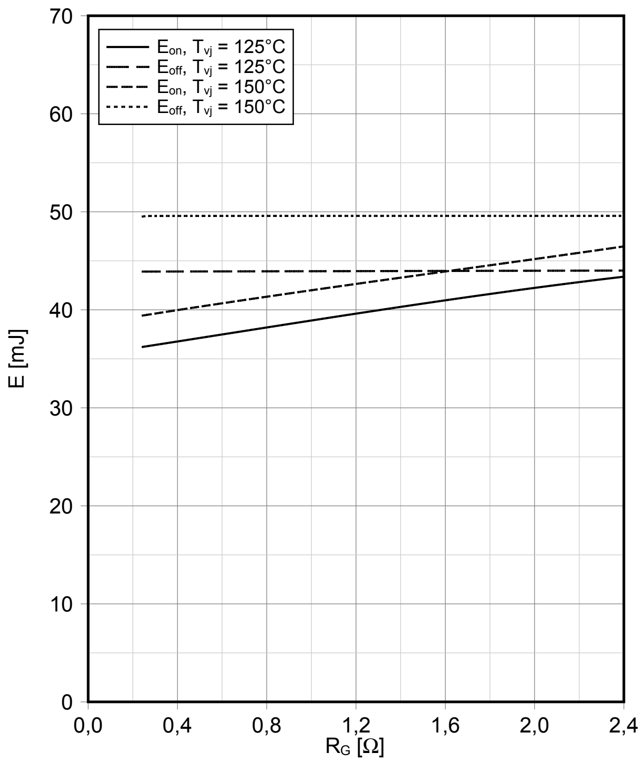
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT,Inverter (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



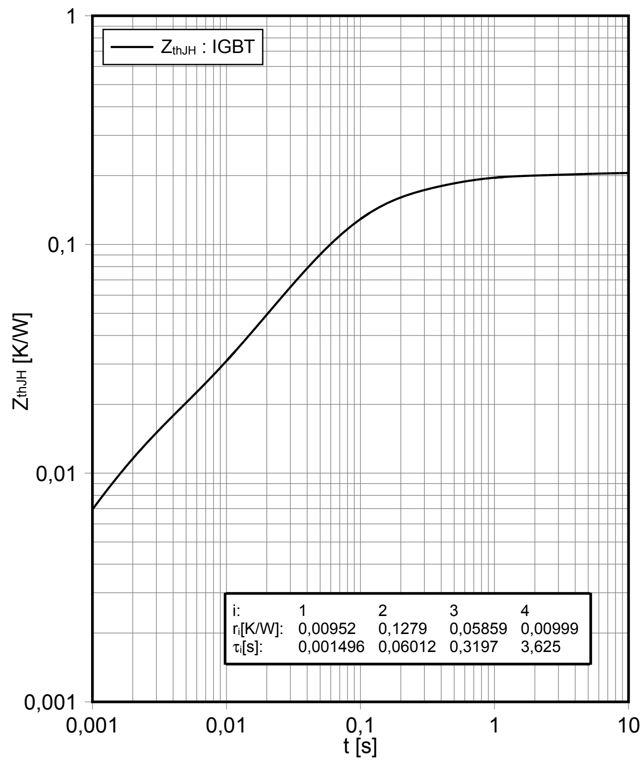
开关损耗 IGBT, 逆变器 （典型)
switching losses IGBT,Inverter (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$V_{GE} = \pm15$ V, $R_{Gon} = 0.24\ \Omega$, $R_{Goff} = 0.24\ \Omega$, $V_{CE} = 900$ V



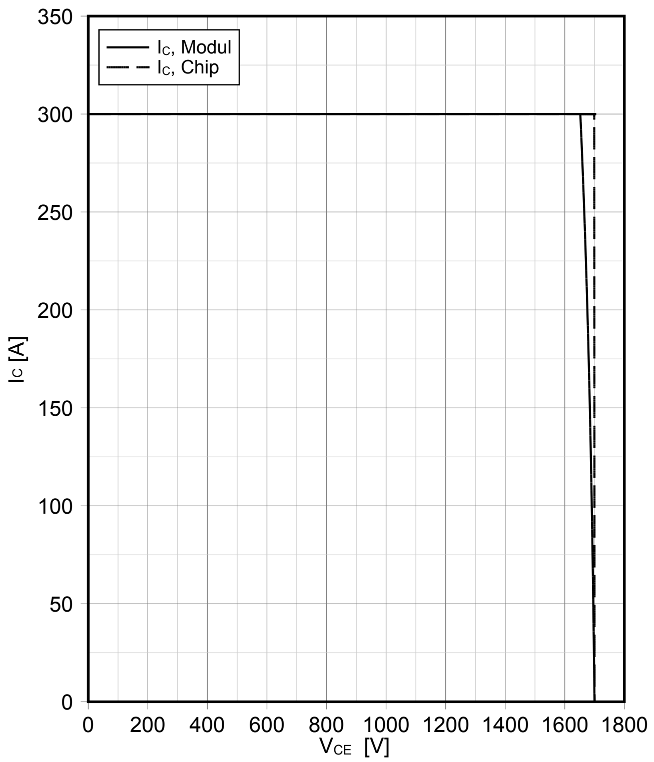
开关损耗 IGBT, 逆变器 （典型)
switching losses IGBT,Inverter (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
$V_{GE} = \pm 15$ V, $I_C = 150$ A, $V_{CE} = 900$ V



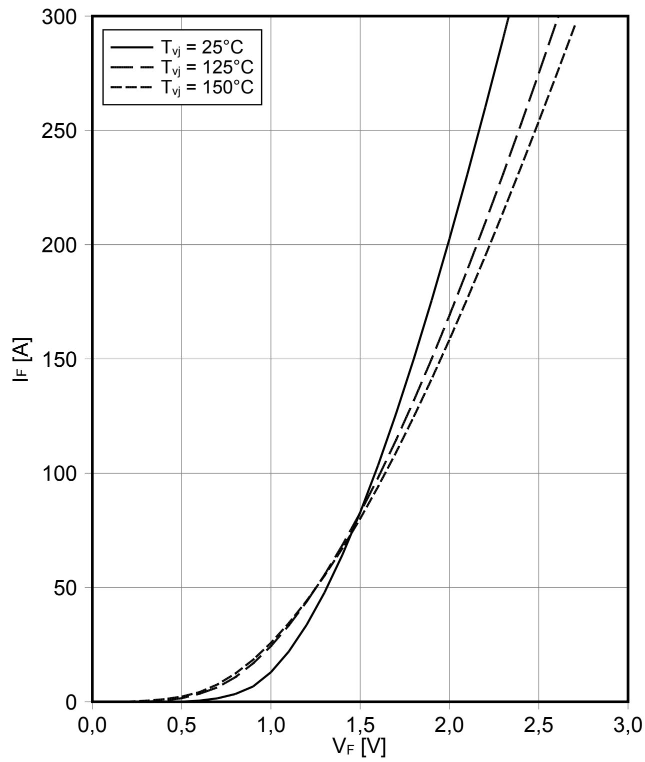
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT,Inverter
$Z_{thJH} = f(t)$



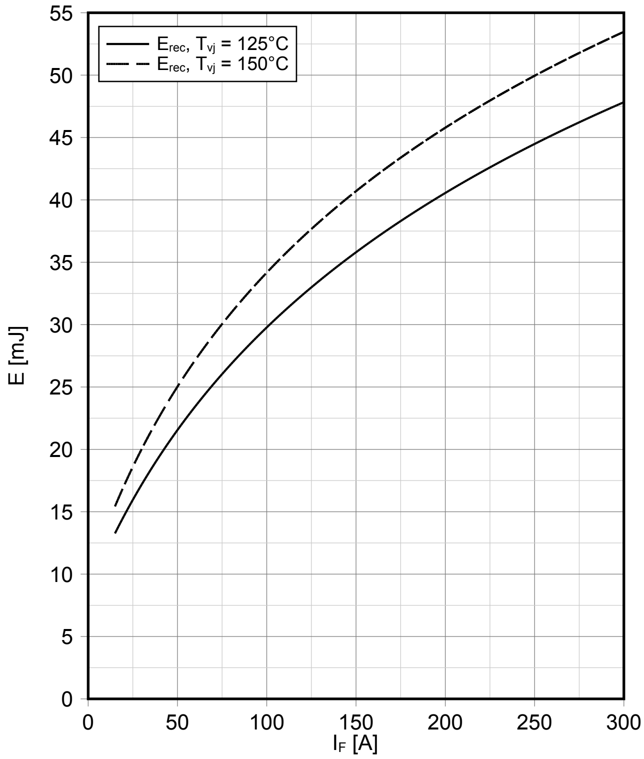
反偏安全工作区 IGBT, 逆变器 （RBSOA）
reverse bias safe operating area IGBT,Inverter (RBSOA)
$I_C = f(V_{CE})$
$V_{GE} = \pm 15$ V, $R_{Goff} = 0.24\ \Omega$, $T_{vj} = 150°C$



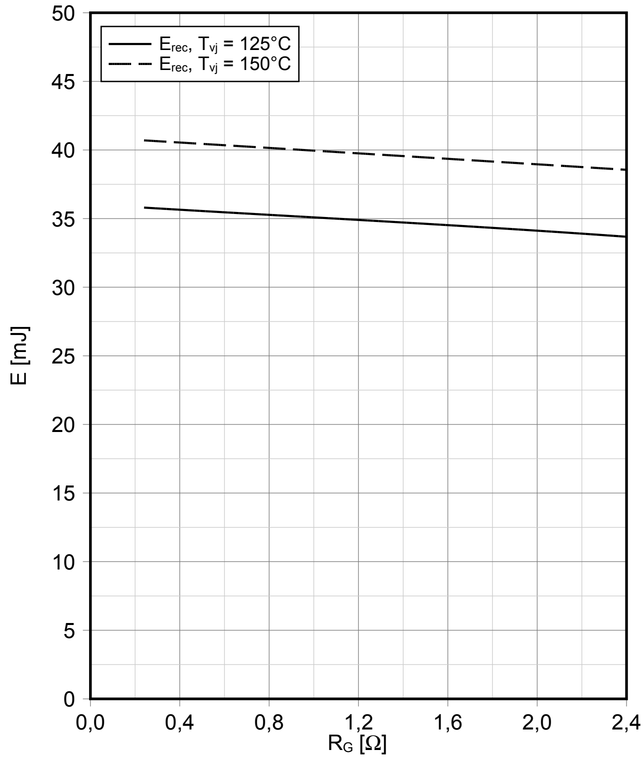
正向偏压特性 二极管,逆变器 （典型)
forward characteristic of Diode, Inverter (typical)
$I_F = f(V_F)$



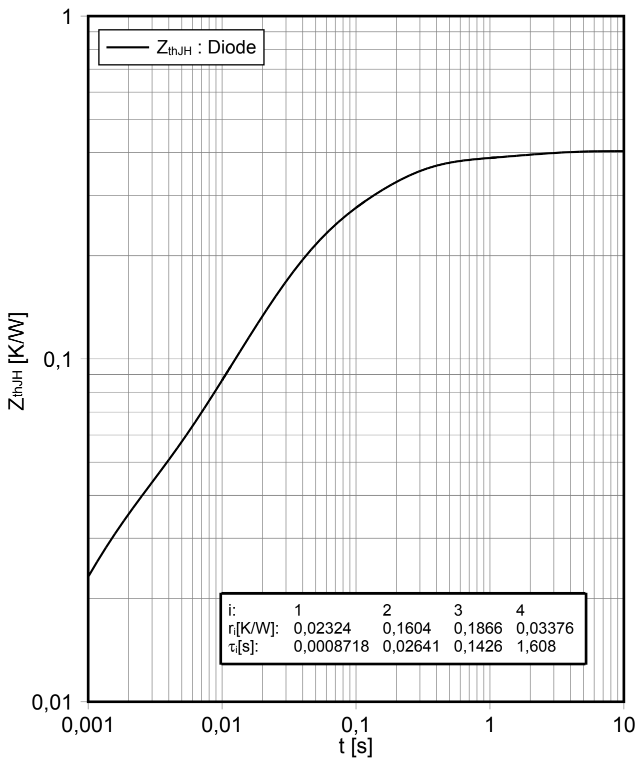
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 0.24\ \Omega$, $V_{CE} = 900$ V



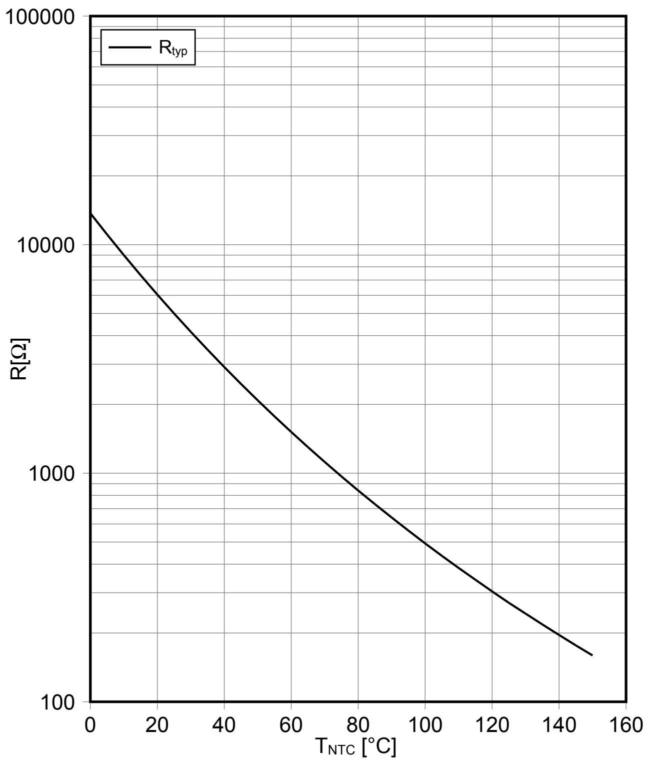
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)
$E_{rec} = f(R_G)$
$I_F = 150$ A, $V_{CE} = 900$ V



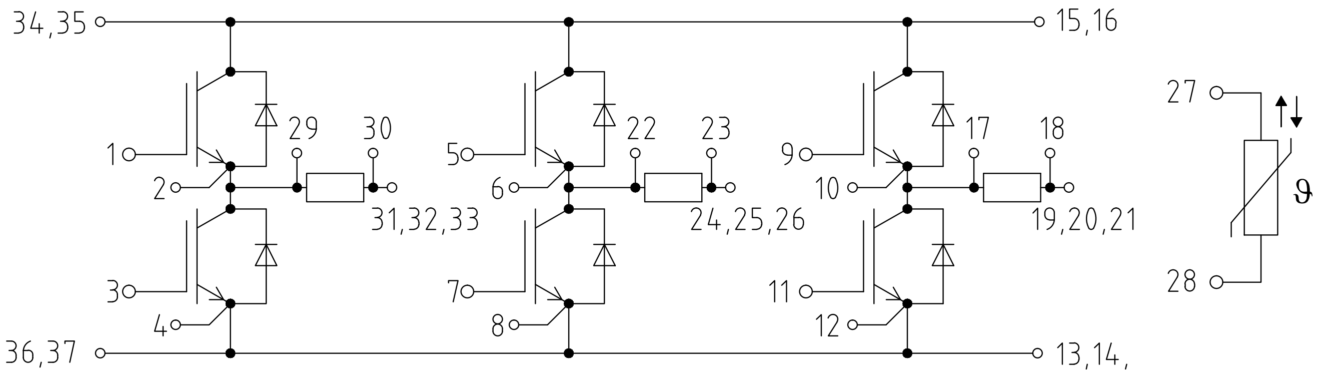
瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter
$Z_{thJH} = f(t)$



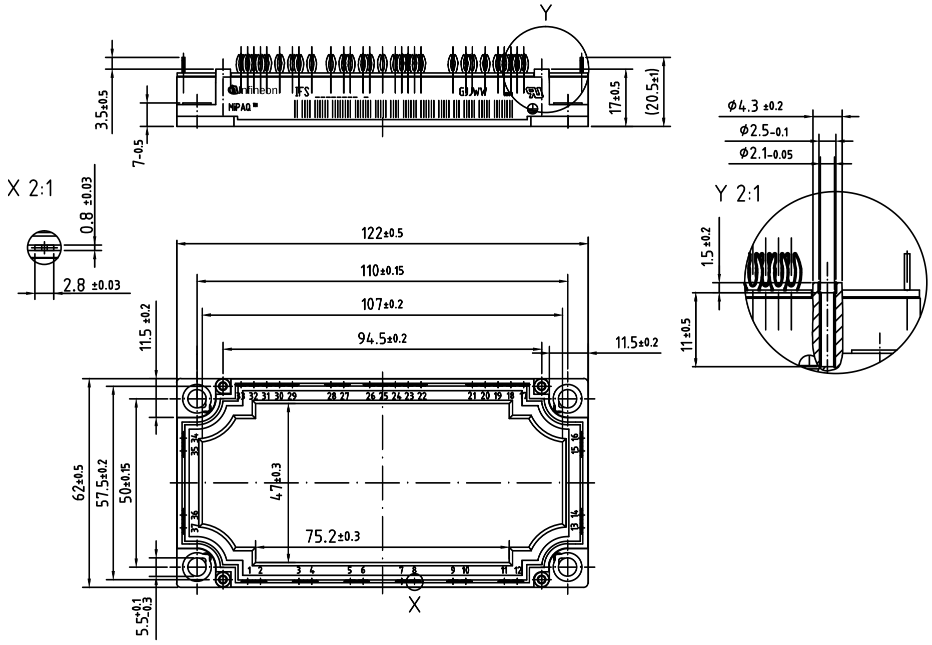
负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)
$R = f(T)$

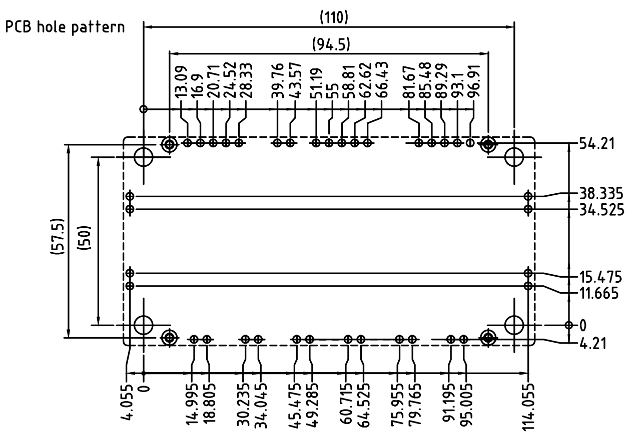


接线图 / Circuit diagram

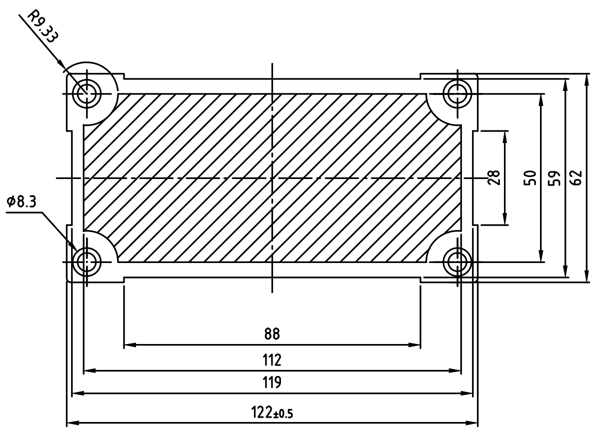


封装尺寸 / Package outlines





- Tolerance of PCB hole pattern ⌖ Ø0.1
- hole specifications see AN 2007-09
- Diameters of plated holes Ø 2.14mm - 2.29mm
- Diameter of drill Ø 2.35mm



restricted area for Thermal Interface Material

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